

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A semiconductor component comprising a semiconductor chip made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises;

an inner connection metallization in a contact window, and said inner connection metallization of said semiconductor chip is connected to a respective outer connection metallization by a wire bond connection; and

~~characterized in that the inner connection metallization comprises a reinforcing system~~ formed from a different material than the inner connection metallization and that ~~has~~ having an open grid structure on the doped silicon substrate, wherein the open grid structure leaves portions of ~~exposes~~ the doped silicon substrate exposed;

~~wherein to direct contact with the inner connection metallization is in direct~~ contact with the doped silicon substrate at the exposed portions of the doped silicon substrate.

2. (original) A semiconductor component as claimed in claim 1, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

3. (original) A semiconductor component as claimed in claim 1, characterized in that the grid structure is formed so as to be an open groove structure.

4. (original) A semiconductor component as claimed in claim 1, characterized in that the grid structure may be formed so as to be an open tube structure.

5. (original) A semiconductor component as claimed in claim 1, characterized in that the

area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

6. (previously presented) A semiconductor component as claimed in claim 1, wherein the open grid structure comprises grid lands and wherein a ratio of height, h, to width, b, of the grid lands is in the range of 1:25 to 1:50.

7. (previously presented) A semiconductor component as claimed in claim 1, wherein the open grid structure comprises grid lands and grid openings and wherein the ratio between the area of the grid lands and the area of the grid openings is greater than 70%.

8. (previously presented) A semiconductor component as claimed in claim 1, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the doped silicon substrate.

9. (currently amended) A semiconductor component comprising a semiconductor chip made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises:

an inner connection metallization in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection; and

~~characterized in that the inner connection metallization comprises a reinforcing system~~ formed from a different material than the inner connection metallization and that has having an open grid structure on the doped silicon substrate, wherein the open grid structure forms at least one opening that leaves the doped silicon substrate exposed;

~~wherein within which~~ the inner connection metallization is in direct contact with the doped silicon substrate within the at least one opening of the reinforcing system.

10. (previously presented) A semiconductor component as claimed in claim 9, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

11. (previously presented) A semiconductor component as claimed in claim 9, characterized in that the grid structure is formed so as to be an open groove structure.

12. (previously presented) A semiconductor component as claimed in claim 9, characterized in that the grid structure may be formed so as to be an open tube structure.

13. (previously presented) A semiconductor component as claimed in claim 9, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

14. (currently amended) A semiconductor component comprising:

discrete semiconductor device comprising:

a silicon substrate having an emitter and a base;

the emitter having an emitter contact formed thereon, the emitter contact comprising an inner connection metallization and a reinforcing system formed from a different material than the inner connection metallization and having an open grid structure, wherein the open grid structure exposes-leaves portions of the emitter exposed, and wherein the silicon substrate to direct contact with the inner connection metallization is in direct contact with the emitter at the exposed portions of the emitter;

the base having a base contact formed thereon, the base contact comprising an inner connection metallization and a reinforcing system formed from a different material than the inner connection metallization and having an open grid structure, wherein the open grid structure exposes leaves portions of the base exposed, and wherein the silicon substrate to direct contact with the inner connection metallization is in direct contact with the base at the exposed portions of the base;

a leadframe having connection pins; and

a bond wire connected between the emitter contact and a connection pin of the leadframe; and

a bond wire connected between the base contact and the a connection pin of the leadframe.

15. (previously presented) A semiconductor component as claimed in claim 14, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.

16. (previously presented) A semiconductor component as claimed in claim 14, characterized in that the grid structure is formed so as to be an open groove structure.

17. (previously presented) A semiconductor component as claimed in claim 14, characterized in that the grid structure may be formed so as to be an open tube structure.

18. (previously presented) A semiconductor component as claimed in claim 14, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.

19. (previously presented) A semiconductor component as claimed in claim 14, wherein the open grid structure of the reinforcing system comprises oxide lands formed directly on the silicon substrate.